L Number	Hits	Search Text	DB	Time stamp
- NOUNCT	19031	(cmp or polish or polishing or planarize	USPAT	2003/09/24
	15001	or planarizing) and test		11:24
_	1653		USPAT	2003/09/12
•		or planarizing).ab. and test		15:38
	205		USPAT	2003/09/12
		or planarizing).ab. and test) and (trench		15:39
_	1	or STI)	USPAT	2002/00/12
	_	(((cmp or polish or polishing or planarize or planarizing).ab. and test)	USPAL	2003/09/12 15:39
		and (trench or STI)) and (reclaim or		10.55
		reclaiming)		
_	193	(((cmp or polish or polishing or	USPAT	2003/09/12
		planarize or planarizing).ab. and test)		15:42
	100	and (trench or STI)) and semiconductor	***************************************	0000/00/15
-	189	((((cmp or polish or polishing or planarize or planarizing).ab. and test)	USPAT	2003/09/15
		and (trench or STI)) and semiconductor)		11:31
		and @ay<=2001		:
_	3681	(cmp or polish or polishing or planarize	USPAT	2003/09/15
		or planarizing).ab. and pattern		15:07
· <del>-</del>	1169	((cmp or polish or polishing or planarize	USPAT	2003/09/15
	·	or planarizing).ab. and pattern) and		11:36
_	922	(trench or STI) (((cmp or polish or polishing or	IICDAM	2002/00/15
	922	planarize or planarizing).ab. and	USPAT	2003/09/15
		pattern) and (trench or STI)) and		10.20
		((silicon adj oxide) or SiO or SiO?sub.2		
		or (silicon adj dioxide))		
_	127	(((cmp or polish or polishing or	USPAT	2003/09/15
		planarize or planarizing).ab. and		11:58
		pattern) and (trench or STI)) and ((silicon adj oxide) or SiO or SiO?sub.2		
		or (silicon adj dioxide))) and		
		sacrificial		
<del>-</del>	1992	((cmp or polish or polishing or planarize	USPAT	2003/09/15
		or planarizing).ab. and pattern) and		11:58
		((silicon adj oxide) or SiO or SiO?sub.2		
	196	or (silicon adj dioxide)) (((cmp or polish or polishing or	TICDAM	2002/00/15
	150	planarize or planarizing).ab. and	USPAT	2003/09/15 12:02
		pattern) and ((silicon adj oxide) or SiO		12.02
•		or SiO?sub.2 or (silicon adj dioxide)) )		
		and sacrificial		
_	178	((((cmp or polish or polishing or	USPAT	2003/09/15
	[	planarize or planarizing).ab. and pattern) and ((silicon adj oxide) or SiO		12:02
		or SiO?sub.2 or (silicon adj dioxide)))		
		and sacrificial) and @ay<=2000		
-	18	((cmp or polish or polishing or planarize	USPAT	2003/09/15
		or planarizing).ab. and pattern) and		13:31
_	100	(reclaim or reclaimed or reclaimation)	11002 =	0000/00/15
	498	(cmp or polish or polishing or planarize or planarizing) and (reclaim or	USPAT	2003/09/15 13:33
		reclaiming or reclaimed or reclaimation)		13:33
-	88	((cmp or polish or polishing or planarize	USPAT	2003/09/15
		or planarizing) and (reclaim or	<del></del>	13:39
		reclaiming or reclaimed or reclaimation))		
		and ((silicon adj oxide) or SiO or		
	81	SiO?sub.2 or (silicon adj dioxide)) (((cmp or polish or polishing or	IICDam	2002/00/15
		planarize or planarizing) and (reclaim or	USPAT	2003/09/15 13:39
		reclaiming or reclaimed or reclaimation))		13.33
	ļ	and ((silicon adj oxide) or SiO or		,
		SiO?sub.2 or (silicon adj dioxide)) ) and		
_		@ay<=2000	•••	
<del></del>	86	(cmp or polish or polishing or planarize or planarizing).ab. and (test with	USPAT	2003/09/15
		pattern)		13:54
····	L			<u> </u>

_	85	((cmp or polish or polishing or planarize	USPAT	2003/09/15
		or planarizing).ab. and (test with		13:54
		pattern)) not (((cmp or polish or		
		polishing or planarize or planarizing)		
		and (reclaim or reclaiming or reclaimed		
	·	or reclaimation)) and ((silicon adj		
		oxide) or SiO or SiO?sub.2 or (silicon		
		adj dioxide)) ) and @ay<=2000)		
	74	, , , , , , , , , , , , , , , , , , ,	USPAT	2003/09/15
		planarize or planarizing).ab. and (test		14:03
		with pattern)) not (((cmp or polish or		
		polishing or planarize or planarizing)		
		and (reclaim or reclaiming or reclaimed		
		or reclaimation)) and ((silicon adj		
		oxide) or SiO or SiO?sub.2 or (silicon		
		adj dioxide)) ) and @ay<=2000)) and @ay<=2000		
	6		IICDAM	2002/00/15
		Lacy-Michael-S.in.	USPAT	2003/09/15 14:03
_	56	("3753269"   "4318250"   "4510113"	TIC DAM	
	. 50	"4576612"   "4672985"   "4720939"	USPAT	2003/09/15 14:48
		"4728552"   "4753838"   "4841680"		14:40
		"4927432"   "4934102"   "4954141"		
		"4962562"   "5020283"   "5081051"		
		"5104421"   "5177908"   "5197999"		
		"5212910"   "5234867"   "5257478"	]	
		"5287663"   "5329734"   "5335453"		
		"5433651"   "5484323"   "5487697"		
		"5489233"   "5531635"   "5534106"		
		"5536202"   "5547417"   "5558568"		
		"5575707"   "5578362"   "5593344"		
		"5605760"   "5611943"   "5622526"		
		"5643044"   "5655951"   "5692947"		
		"5692950"   "5725417"   "5759918"		
		"5762536"   "5779526"   "5810964"		
		"5871390"   "5897426"   "5899798"		
		"5908530"   "5958794"   "6093651"		
		"6106351"   "6206759").PN.		
_	2821	(cmp or polish or polishing or planarize	USPAT	2003/09/15
	1700	or planarizing) and sacrificial		15:07
-	1700	((cmp or polish or polishing or planarize	USPAT	2003/09/15
		or planarizing) and sacrificial) and		15:09
		((strip or stripping or remove or		
		removing or etch or etching) with	,	
	402	sacrificial)	TIGDA III	0000 (00 (15
	402	((cmp or polish or polishing or planarize	USPAT	2003/09/15
		or planarizing) and sacrificial) and ((strip or stripping or remove or		15:10
		removing or etch or etching) with		
		(sacrificial near oxide))		
-	345	(((cmp or polish or polishing or	USPAT	2003/09/15
		planarize or planarizing) and	001111	15:11
		sacrificial) and ((strip or stripping or		
		remove or removing or etch or etching)		
		with (sacrificial near oxide))) and		
		@ay<=2000		
_	22	(((cmp or polish or polishing or	USPAT	2003/09/15
		planarize or planarizing) and		15:10
		sacrificial) and ((strip or stripping or		
		remove or removing or etch or etching)		
		with (sacrificial near oxide))) and		
	100	<pre>@ay&lt;=2000) and (test or testing)</pre>		
-	182	(((cmp or polish or polishing or	USPAT	2003/09/15
		planarize or planarizing) and		15:24
		sacrificial) and ((strip or stripping or		
		remove or removing or etch or etching)		
	]	with (sacrificial near oxide))) and		
		<pre>@ay&lt;=2000) and ((trench or STI) same sacrificial)</pre>		
_	664	(re\$1claim or re\$1claiming or re\$1claimed	USPAT	2003/09/15
		or reclaimation) and semiconductor	ODIMI	15:25
		,	· · · · · · · · · · · · · · · · · · ·	

_	157	((re\$1claim or re\$1claiming or	USPAT	2003/09/15
	,	re\$1claimed or reclaimation) and		15:26
		semiconductor) and ((silicon adj oxide)		
		or SiO or SiO?sub.2 or (silicon adj		
		dioxide) or sacrificial)		
	147		USPAT	2003/09/15
		re\$1claimed or reclaimation) and		15:26
		semiconductor) and ((silicon adj oxide)		13.20
	İ			
		or SiO or SiO?sub.2 or (silicon adj		
	100	dioxide) or sacrificial) ) and @ay<=2000		
<del>-</del>	499	The second of th	USPAT	2003/09/16
		or planarizing) and (reclaim or		16:32
		reclaiming or reclaimed or reclaimation)		
-	472	((CMP or polishing or polish or planarize	USPAT	2003/09/16
		or planarizing) and (reclaim or		16:33
		reclaiming or reclaimed or reclaimation))		
		and @ay<=2000		
_	111	_	USPAT	2003/09/16
		planarize or planarizing) and (reclaim or	OSPAI	16:34
				16:34
	,	reclaiming or reclaimed or reclaimation))		
		and @ay<=2000) and semiconductor		
-	7	( 332333)   1/30033   30313/3	USPAT	2003/09/16
		"5131979"   "5622875"   "5855735"		16:34
		"5981301").PN.		
_	121		USPAT	2003/09/20
		reclaimation) and (trench or STI)		10:41
_	20	· · · · · · · · · · · · · · · · · · ·	USPAT	2003/09/20
		,	ODIAL	10:46
	7	("3923567"   "4738056"   "5051375"	IICDAM	
	′		USPAT	2003/09/20
		"5131979"   "5622875"   "5855735"		10:47
		"5981301").PN.		
-	11	5131979.URPN.	USPAT	2003/09/20
				10:48
-	921	(cmp or polish or polishing or planarize	USPAT	2003/09/24
		or planarizing) and (test near3 (pattern		11:30
		or structure))		
_	591	, ,	USPAT	2003/09/24
		or planarizing) and (test near3 (pattern	ODITAL	11:27
		or structure))) and (oxide or dioxide or		11.27
	:	Sio or Sio?sub.2)		
	501	•		0000/00/04
	591	, , , , , , , , , , , , , , , , , , ,	USPAT	2003/09/24
		planarize or planarizing) and (test near3		11:29
		(pattern or structure))) and (oxide or		
		dioxide or SiO or SiO?sub.2) ) and (cmp		
		or polish or polishing or planarize or		
		planarizing or planarization)		
-	517	((((cmp or polish or polishing or	USPAT	2003/09/24
		planarize or planarizing) and (test near3		11:29
		(pattern or structure))) and (oxide or		
	•	dioxide or SiO or SiO?sub.2) ) and (cmp		
-		or polish or polishing or planarize or		
		planarizing or planarization)) and		
		(silicon or semiconductor)		
_	87		I I C D A FE	2002/00/04
}	07	(((((cmp or polish or polishing or	USPAT	2003/09/24
		planarize or planarizing) and (test near3		13:17
		(pattern or structure))) and (oxide or		
		dioxide or SiO or SiO?sub.2) ) and (cmp		
		or polish or polishing or planarize or		
		planarizing or planarization)) and		
1		(silicon or semiconductor)) and ((cmp or		
		polish or polishing or planarize or		
		planarizing) same(test near3 (pattern or		
		structure)))		
_	15	1	USPAT	2003/09/24
		"5665633"   "5747380"   "5885856"		11:31
		"5923563"   "5948573"   "5956618"		
		"5970238"   "6087733"   "6232161"		
		"6281049"   "6448630"   "6486066").PN.		
_	6	· ·	Hanam	1 2002 (22 (2)
	8	("5736427"   "6136709"   "6214716"	USPAT	2003/09/24
	<u>.</u>	"6274483"   "6297156"   "6306737").PN.		11:41

_	3821	(sacrifice or sacrificial) with (oxide or	USPAT	2003/09/24
		dioxide or SiO or SiO?sub.2)		13:19
-	3043	((sacrifice or sacrificial) with (oxide	USPAT	2003/09/24
		or dioxide or SiO or SiO?sub.2)) and		13:19
		semiconductor		
_	8	((sacrifice or sacrificial) with (oxide	USPAT	2003/09/24
		or dioxide or SiO or SiO?sub.2)) and		13:20
		(re\$1claim or re\$1claiming or re\$1claimed		
		or re\$1claimation)		
-	144	, , , , , , , , , , , , , , , , , , ,	USPAT	2003/09/24
	:	or re\$1claimation) near4 (substrate or		13:21
		wafer)		
_	134	((re\$1claim or re\$1claiming or	USPAT	2003/09/24
		re\$1claimed or re\$1claimation) near4		15:06
		(substrate or wafer)) and @ay<=2000		,
	1	6451696.pn.	USPAT	2003/09/24
				15:24
-	4	("3715842"   "3923567"   "5622875"	USPAT	2003/09/24
1		"5855735").PN.		15:07
-	237523	transistor	USPAT	2003/09/24
				15:24
-	168	transistor and (reclaim or reclaiming)	USPAT	2003/09/24
				15:24